Zakhar D Kovalyuk

List of Publications by Year
in descending order

218 papers	4,187 citations	257101 24 h-index	128067 60 g-index
226 all docs	226 docs citations	226 times ranked	4442 citing authors

#	Article	IF	Citations
1	High electron mobility, quantum Hall effect and anomalous optical response in atomically thin InSe. Nature Nanotechnology, 2017, 12, 223-227.	15.6	996
2	Tuning the Bandgap of Exfoliated InSe Nanosheets by Quantum Confinement. Advanced Materials, 2013, 25, 5714-5718.	11.1	512
3	High Broadâ€Band Photoresponsivity of Mechanically Formed InSeâ€“Graphene van der Waals Heterostructures. Advanced Materials, 2015, 27, 3760-3766.	11.1	320
4	The direct-to-indirect band gap crossover in two-dimensional van der Waals Indium Selenide crystals. Scientific Reports, 2016, 6, 39619.	1.6	150
5	Design of van der Waals interfaces for broad-spectrum optoelectronics. Nature Materials, 2020, 19, 299-304.	13.3	106
6	Epitaxial growth of Î³ -InSe and Î± , Î² , and Î³ -In ₂ Se ₃ on Îµ -GaSe. 2D Materials, 2018, 5, 035026.	2.0	98
7	Quantum confinement and photoresponsivity of Î² -In ₂ Se ₃ nanosheets grown by physical vapour transport. 2D Materials, 2016, 3, 025030.	2.0	88
8	Engineering p â€“ n junctions and bandgap tuning of InSe nanolayers by controlled oxidation. 2D Materials, 2017, 4, 025043.	2.0	76
9	Room Temperature Electroluminescence from Mechanically Formed van der Waals IIIâ€“VI Homojunctions and Heterojunctions. Advanced Optical Materials, 2014, 2, 1064-1069.	3.6	71
10	Interlayer Bandâ€toâ€Band Tunneling and Negative Differential Resistance in van der Waals BP/InSe Fieldâ€Effect Transistors. Advanced Functional Materials, 2020, 30, 1910713.	7.8	65
11	Electronic band structure of GaSe(0001):â€,â€,Angle-resolved photoemission andab initiotheory. Physical Review B, 2003, 68, .	1.1	61
12	Large Tunneling Magnetoresistance in van der Waals Ferromagnet/Semiconductor Heterojunctions. Advanced Materials, 2021, 33, e2104658.	11.1	61
13	Quantum confined acceptors and donors in InSe nanosheets. Applied Physics Letters, 2014, 105, 221909.	1.5	58
14	Giant Quantum Hall Plateau in Graphene Coupled to an InSe van der Waals Crystal. Physical Review Letters, 2017, 119, 157701.	2.9	44
15	Electrical and photoelectrical properties of photosensitive heterojunctions n-TiO₂/p-CdTe. Semiconductor Science and Technology, 2011, 26, 125006.	1.0	41
16	Gate-Defined Quantum Confinement in InSe-Based van der Waals Heterostructures. Nano Letters, 2018, 18, 3950-3955.	4.5	40
17	Formation and Healing of Defects in Atomically Thin GaSe and InSe. ACS Nano, 2019, 13, 5112-5123.	7.3	35
18	Two-Dimensional Covalent Crystals by Chemical Conversion of Thin van der Waals Materials. Nano Letters, 2019, 19, 6475-6481.	4.5	32

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19	Biexciton formation and exciton coherent coupling in layered GaSe. Journal of Chemical Physics, 2015, 142, 212422.	1.2	31
20	Coherent acoustic phonons in van der Waals nanolayers and heterostructures. Physical Review B, 2018, 98, .	1.1	31
21	Intrinsic conductive oxideâ€“p-InSe solar cells. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 252-255.	1.7	29
22	Mechanisms of charge transport in anisotype n-TiO2/p-CdTe heterojunctions. Semiconductors, 2011, 45, 1077-1081.	0.2	29
23	Native oxide emerging of the cleavage surface of gallium selenide due to prolonged storage. Semiconductors, 2008, 42, 414-421.	0.2	26
24	Formation of nanostructure on the surface of layered InSe semiconductor caused by oxidation under heating. Physics of the Solid State, 2007, 49, 1572-1578.	0.2	24
25	Optical constants and polarimetric properties of Đ¢Ñ–Đž2â€“MnO2 thin films. Optical Materials, 2012, 34, 1940-1945.	1.7	24
26	Graphitic carbon/n-CdTe Schottky-type heterojunction solar cells prepared by electron-beam evaporation. Solar Energy, 2015, 112, 78-84.	2.9	24
27	High-Frequency Elastic Coupling at the Interface of van der Waals Nanolayers Imaged by Picosecond Ultrasonics. ACS Nano, 2019, 13, 11530-11537.	7.3	24
28	Mechanism of excitonic dephasing in layered InSe crystals. Physical Review B, 2014, 89, .	1.1	23
29	Light-dependentIâ€“Vcharacteristics of TiO₂/CdTe heterojunction solar cells. Semiconductor Science and Technology, 2012, 27, 055008.	1.0	22
30	Resonant tunnelling into the two-dimensional subbands of InSe layers. Communications Physics, 2020, 3, .	2.0	22
31	Optical properties of TiO2-MnO2 thin films prepared by electron-beam evaporation. Technical Physics, 2012, 57, 1148-1151.	0.2	20
32	Photoquantum Hall Effect and Lightâ€Induced Charge Transfer at the Interface of Graphene/InSe Heterostructures. Advanced Functional Materials, 2019, 29, 1805491.	7.8	20
33	Electrical properties of anisotype heterojunctions n-CdZnO/p-CdTe. Semiconductors, 2012, 46, 1152-1157.	0.2	18
34	Van der Waals SnSe 2(1â^' x) S 2 x Alloys: Compositionâ€Dependent Bowing Coefficient and Electronâ€“Phonon Interaction. Advanced Functional Materials, 2020, 30, 1908092.	7.8	18
35	Twoâ€Dimensional Character of Electron Gas in Layered InSe Crystals. Physica Status Solidi (B): Basic Research, 1990, 162, 213-225.	0.7	17
36	Enhanced Optical Emission from 2D InSe Bent onto Siâ€Pillars. Advanced Optical Materials, 2020, 8, 2000828.	3.6	17

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37	Magnetic properties and surface morphology of layered In2Se3 crystals intercalated with cobalt. Physics of the Solid State, 2013, 55, 1148-1155.	0.2	16
38	Ferroelectric semiconductor junctions based on graphene/In₂Se₃/graphene van der Waals heterostructures. 2D Materials, 2021, 8, 045020.	2.0	16
39	On some physical properties of InSe and GaSe semiconducting crystals intercalated by ferroelectrics. Journal of Physics Condensed Matter, 1997, 9, L191-L195.	0.7	15
40	Anomalies of magnetic properties of layered crystals InSe containing Mn. Materials Science and Engineering C, 2007, 27, 1052-1055.	3.8	15
41	Self-organization of PbTe and SnTe nanostructures on the van der Walls GaSe(0001) surface. Technical Physics Letters, 2007, 33, 86-90.	0.2	15
42	Surface topology of GaSe oxidized crystals. Superlattices and Microstructures, 2008, 44, 416-419.	1.4	15
43	Temperature dependent electrical properties and barrier parameters of photosensitive heterojunctions n-TÑ–N/p-Cd_{1â^'x}Zn_xTe. Semiconductor Science and Technology, 2015, 30, 075006.	1.0	15
44	Anomalous Low Thermal Conductivity of Atomically Thin InSe Probed by Scanning Thermal Microscopy. Advanced Functional Materials, 2021, 31, 2008967.	7.8	15
45	On the mechanisms of current transfer in n-In2Se3-p-GaSe heterostructures. Technical Physics Letters, 2002, 28, 707-710.	0.2	14
46	Effect of gamma radiation on the properties of InSe photodiodes. Technical Physics Letters, 2005, 31, 359-360.	0.2	14
47	Ferromagnetic states in theIn1â^'xMnxSelayered crystal. Physical Review B, 2005, 71, .	1.1	14
48	Ferromagnetism of layered GaSe semiconductors intercalated with cobalt. Semiconductors, 2012, 46, 971-974.	0.2	14
49	Nanomechanical probing of the layer/substrate interface of an exfoliated InSe sheet on sapphire. Scientific Reports, 2016, 6, 26970.	1.6	14
50	Photoluminescence dynamics in few-layer InSe. Physical Review Materials, 2020, 4, .	0.9	14
51	Emission of free and bound excitons in layered gase crystals. Physica Status Solidi (B): Basic Research, 1983, 117, 283-287.	0.7	13
52	Polarisation-sensitive photodiode for the 632.8 nm spectral region. Electronics Letters, 1990, 26, 664-664.	0.5	13
53	2D nanocomposite photoconductive sensors fully dry drawn on regular paper. Nanotechnology, 2015, 26, 255501.	1.3	13
54	Improved performance of InSe field-effect transistors by channel encapsulation. Semiconductor Science and Technology, 2018, 33, 06LT01.	1.0	13

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55	Schottky-barrier thin-film transistors based on HfO2-capped InSe. Applied Physics Letters, 2019, 115, .	1.5	13
56	Influence of Ni Impurity on the Absorption Spectrum of Layered GaSe Crystals. Physica Status Solidi (B): Basic Research, 1981, 106, 621-626.	0.7	12
57	Electrical properties of In2Se3 layered crystals doped with cadmium, iodine, or copper. Inorganic Materials, 2007, 43, 1271-1274.	0.2	12
58	Properties of Hydrogenated GaSe Crystals. Inorganic Materials, 2005, 41, 793-795.	0.2	11
59	The formation of organic (propolis films)/inorganic (layered crystals) interfaces for optoelectronic applications. Superlattices and Microstructures, 2008, 44, 563-570.	1.4	11
60	Graphene-InSe-graphene van der Waals heterostructures. Journal of Physics: Conference Series, 2015, 647, 012001.	0.3	11
61	The Interaction of Hydrogen with the van der Waals Crystal Î³-InSe. Molecules, 2020, 25, 2526.	1.7	11
62	APPLICATION OF LAYERED InSe AND GaSe CRYSTALS AND POWDERS FOR SOLID STATE HYDROGEN STORAGE. , 2007, , 325-340.		11
63	NMR study of the chargeâ€densityâ€wave state in VSe₂. Physica Status Solidi (B): Basic Research, 1983, 119, 401-410.	0.7	10
64	Space-Charge Region Scattering in Indium Monoselenide. Physica Status Solidi A, 2000, 180, 523-531.	1.7	10
65	Photoresponse spectral investigations for anisotropic semiconductor InSe. Optical Materials, 2001, 17, 279-281.	1.7	10
66	Structural and optical characterization of the propolis films. Applied Surface Science, 2006, 253, 279-282.	3.1	10
67	Surfaceâ€“barrier heterojunctions TiO₂/CdZnTe. Semiconductor Science and Technology, 2013, 28, 015014.	1.0	10
68	Highly-mismatched InAs/InSe heterojunction diodes. Applied Physics Letters, 2016, 109, .	1.5	10
69	Influence of Intercalation by Metallic Atoms on the Shubnikov -de Haas Effect and the Energy Spectrum of Bi2Te3. Physica Status Solidi (B): Basic Research, 1992, 169, 157-162.	0.7	9
70	Annealing effect on conductivity anisotropy in indium selenide single crystals. Physica Status Solidi A, 1996, 155, 451-460.	1.7	9
71	Influence of self-oxide formation regimes on the properties of oxide-p-InSe heterojunctions. Technical Physics Letters, 1999, 25, 520-521.	0.2	9
72	The effect of photocurrent amplification in an In2O3-GaSe heterostructure. Technical Physics Letters, 2001, 27, 755-757.	0.2	9

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73	Electrical and photoelectric characteristics of structures based on InSe and GaSe layered semiconductors irradiated with 12.5-MeV electrons. Semiconductors, 2008, 42, 1292-1297.	0.2	9
74	Neutron diffraction studies of the negative thermal expansion in a layered indium selenide crystal. Physics of the Solid State, 2009, 51, 2342-2346.	0.2	9
75	Tunable spin-orbit coupling in two-dimensional InSe. Physical Review B, 2021, 104, .	1.1	9
76	Variation in the built-in potential of a photodiode based on an n-InSe-p-GaSe heterojunction in the course of aging. Semiconductors, 2004, 38, 546-549.	0.2	8
77	Weak ferromagnetism in InSe:Mn layered crystals. Semiconductors, 2005, 39, 772-776.	0.2	8
78	Spectroscopic studies of 2H-PbI2(Mn) layered crystals. Physica Status Solidi (B): Basic Research, 2005, 242, 2427-2432.	0.7	8
79	Age-induced oxide on cleaved surface of layered GaSe single crystals. Applied Surface Science, 2008, 254, 2067-2071.	3.1	8
80	Electrical properties of hybrid (ferromagnetic metal)â€"(layered semiconductor) Ni/pâ€"GaSe structures. Semiconductors, 2010, 44, 171-183.	0.2	8
81	Crystal growth and elastic properties of In2Se3. Inorganic Materials, 2011, 47, 1174-1177.	0.2	8
82	Fabrication and Characterization of Photosensitive n-CdO/p-InSe Heterojunctions. Acta Physica Polonica A, 2013, 124, 720-723.	0.2	8
83	Effect of low-temperature annealing on the quality of InSe layered single crystals and the characteristics of n-InSe/p-InSe heterojunctions. Semiconductors, 2014, 48, 545-550.	0.2	8
84	Heat capacity of then-InSe single crystal layered semiconductor. Journal of Applied Physics, 2002, 92, 5110-5112.	1.1	7
85	Energy band diagram of a photosensitive Sn-p-InSe structure. Technical Physics Letters, 2003, 29, 480-484.	0.2	7
86	Photosensitivity of the semiconductor-turpentine heterocontact. Technical Physics Letters, 2004, 30, 250-252.	0.2	7
87	Î³-Radiation influence on the photoelectrical properties of oxideâ€"p-InSe heterostructure. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 118, 147-149.	1.7	7
88	Optical and photoelectric properties of barium-intercalated InSe and GaSe. Inorganic Materials, 2009, 45, 1222-1225.	0.2	7
89	On the Possibility of Layered Crystals Application for Solid State Hydrogen Storages - InSe and GaSe Crystals. , 0, , .		7
90	Magnetotransport and lateral confinement in an InSe van der Waals Heterostructure. 2D Materials, 2018, 5, 035040.	2.0	7

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91	N-shaped volt-ampere characteristics of InSe single crystals at low temperatures. Solid State Communications, 1990, 75, 465-467.	0.9	6
92	Optical and electrical properties of propolis films. Technical Physics, 2004, 49, 1529-1530.	0.2	6
93	Surface structure of unoxidized and oxidized Bi2Se3 crystals. Inorganic Materials, 2010, 46, 1296-1298.	0.2	6
94	Carrier transport in layered semiconductor (p-GaSe)-ferroelectric (KNO3) composite nanostructures. Semiconductors, 2011, 45, 338-349.	0.2	6
95	Temperature and baric dependence of nuclear quadruple resonance spectra in indium and gallium monoselenides. , 2013, , .		6
96	Structure of oxidized and unoxidized end faces of GaSe layered crystals. Inorganic Materials, 2014, 50, 339-343.	0.2	6
97	Electrical and Photoelectric Properties of the TiN/p-InSe Heterojunction. Semiconductors, 2016, 50, 334-338.	0.2	6
98	Prompt quality monitoring of InSe and GaSe semiconductor crystals by the nuclear quadrupole resonance technique. Semiconductors, 2016, 50, 1034-1037.	0.2	6
99	Room Temperature Uniaxial Magnetic Anisotropy Induced By Feâ€Islands in the InSe Semiconductor Van Der Waals Crystal. Advanced Science, 2018, 5, 1800257.	5.6	6
100	Resonance and antiresonance in Raman scattering in GaSe and InSe crystals. Scientific Reports, 2021, 11, 924.	1.6	6
101	Alkaliâ€Metalâ€Intercalated Indium and Gallium Selenides Nonâ€Monotonous Shift of Exciton Lines. Physica Status Solidi (B): Basic Research, 1989, 155, 717-722.	0.7	5
102	p-GaSe-n-recrystallized InSe heterojunctions. Technical Physics Letters, 2000, 26, 54-55.	0.2	5
103	Oxide-p-InSe heterostructures with improved photoelectric characteristics. Semiconductors, 2004, 38, 402-405.	0.2	5
104	Effect of the buffer layer of GaSe intrinsic oxide with nanometer thickness on electrical, photoelectric, and emissive properties of ITO-GaSe heterostructures. Semiconductors, 2007, 41, 301-306.	0.2	5
105	The effect of neutron radiation on the photoelectric parameters of ITO-GaSe structures. Semiconductors, 2007, 41, 550-554.	0.2	5
106	Effect of neutron radiation on the photoelectric parameters of p-n-InSe structures. Technical Physics Letters, 2007, 33, 767-770.	0.2	5
107	X-ray diffraction study of the molecular propolis films deposited from an alcohol solution onto the cleavage surfaces of layered V2VI3 compounds. Technical Physics, 2008, 53, 1215-1221.	0.2	5
108	Radiation resistance of photodiodes based on indium monoselenides under Î³-irradiation. Journal of Nuclear Materials, 2009, 385, 489-494.	1.3	5

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109	Surface morphology and electrical resistance of the oxide film on InSe. Inorganic Materials, 2011, 47, 749-752.	0.2	5
110	Influence of external factors on the self-organization of lead and tin telluride nanostructures on the BaF2(111) surface under conditions close to the thermodynamic equilibrium. Physics of the Solid State, 2013, 55, 181-195.	0.2	5
111	Photosensitive anisotype n-ZnSe/p-InSe and n-ZnSe/p-GaSe heterojunctions. Technical Physics, 2014, 59, 1205-1208.	0.2	5
112	Nanocomposite structures grown by inserting ionic salt RbNO3 into van der Waals gaps of IIIâ€“VI compound layered semiconductors. Solid State Ionics, 2015, 273, 59-65.	1.3	5
113	Highâ€Performance Phototransistors by Alumina Encapsulation of a 2D Semiconductor with Selfâ€Aligned Contacts. Advanced Electronic Materials, 2022, 8, .	2.6	5
114	On the possibility of the exciton-phonon bound states in GaSe. Solid State Communications, 1980, 33, 621-622.	0.9	4
115	Effect of Laser Irradiation on Lowâ€Temperature Photoconductivity and Photoluminescence Spectra of Gallium Selenide. Physica Status Solidi (B): Basic Research, 1989, 153, 667-673.	0.7	4
116	Optical Properties of GaSe Crystals Containing Mn Impurity Atoms. I. Excitonâ€Phonon Interaction. Physica Status Solidi (B): Basic Research, 1990, 161, 419-426.	0.7	4
117	Optical Properties of GaSe Crystals Containing Mn Impurity Atoms. II. Excitonic and Impurity Emission. Physica Status Solidi (B): Basic Research, 1990, 161, 427-434.	0.7	4
118	â€œIntrinsicâ€•transport properties of InSe studied by millimeter and submillimeter spectroscopy. Solid State Communications, 1998, 105, 433-438.	0.9	4
119	Semiconductor-propolis heterojunction. Technical Physics Letters, 2003, 29, 867-870.	0.2	4
120	Effect of uniaxial compression on the photoconversion parameters in a p-GaSe-n-InSe optical contact. Semiconductors, 2005, 39, 600-602.	0.2	4
121	Electrical properties of hydrogenated InSe crystals. Inorganic Materials, 2006, 42, 1308-1310.	0.2	4
122	X-ray diffraction investigation of the structure of propolis films. Physics of the Solid State, 2006, 48, 1602-1604.	0.2	4
123	A study of isotype photosensitive heterostructures (intrinsic oxide)-n-InSe prepared by long-term thermal oxidation. Semiconductors, 2007, 41, 1056-1059.	0.2	4
124	Experimental investigation of effect of aromatic hydrocarbons on resistivity of indium selenide. Semiconductors, 2007, 41, 1197-1200.	0.2	4
125	Electrical properties of In2Se3âŒ©MnâŒª and InSeâŒ©MnâŒª crystals. Inorganic Materials, 2012, 48, 103-105.	0.2	4
126	Effect of bremsstrahlung Î³-ray photons and neutrons on the parameters of indium-selenium photoconverters. Semiconductors, 2014, 48, 239-244.	0.2	4

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127	Spectral anisotropy of a photoresponse from heterojunctions based on GaSe and InSe layered crystals. Technical Physics, 2014, 59, 407-410.	0.2	4
128	Fine structure of NQR spectra in GaSe. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2009, 12, 370-374.	0.3	4
129	Terahertz control of photoluminescence emission in few-layer InSe. Applied Physics Letters, 2022, 120, .	1.5	4
130	The electrical and photoelectrical properties of n-In2Se3-p-InSe heterostructures. Technical Physics Letters, 2002, 28, 711-713.	0.2	3
131	Optical Investigation of Hydrogen Intercalation-Deinteracalation Processes in Layered Semiconductorl3-InSe Crystals. NATO Science Series Series II, Mathematics, Physics and Chemistry, 2004, , 519-530.	0.1	3
132	Characteristics of the oxide-p-InSe heterojunctions exposed to irradiation with X-ray photons. Semiconductors, 2006, 40, 911-914.	0.2	3
133	Electrical, luminescent and photovoltaic properties of the indium tin oxideâ€“GaSe heterojunctions with a thin layer of gallium oxide. Thin Solid Films, 2007, 515, 6356-6359.	0.8	3
134	Structure and magnetic properties of cobalt-intercalated layered InSe crystals. Technical Physics, 2014, 59, 1462-1465.	0.2	3
135	Electrochemical, optical, and magnetic properties of Ni x InSe (0 < x â‰ 1) intercalation compounds. Inorganic Materials, 2014, 50, 976-980.	0.2	3
136	On the photopleochroism coefficient and its temperature dynamics in native oxide-p-InSe heterojunctions. Semiconductors, 2014, 48, 776-778.	0.2	3
137	Fabrication and characterization of PbSe nanostructures on van der Waals surfaces of GaSe layered semiconductor crystals. Nanotechnology, 2015, 26, 465601.	1.3	3
138	Two-band conduction in electron-irradiated n-InSe single crystals. Physica Status Solidi (B): Basic Research, 2015, 252, 346-356.	0.7	3
139	Ferromagnetism of Narrow-Gap Ge1-x-ySnxMnyTe and Layered In1-xMnxSe Semiconductors. Acta Physica Polonica A, 2008, 114, 1219-1227.	0.2	3
140	The electric field gradient asymmetry parameter in InSe. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2011, 14, 164-166.	0.3	3
141	An Isothermal Annealing Effect on the Luminescence Spectra of GaSe Single Crystals. Physica Status Solidi (B): Basic Research, 1984, 123, K63.	0.7	2
142	Photoelectric properties of the n-SnSSe-p-InSe heterojunctions. Technical Physics Letters, 2000, 26, 754-756.	0.2	2
143	Heterojunctions Produced from the Layered Semiconductors SnS1.9Se0.1and GaSeâ€ˆCdã€‰. Inorganic Materials, 2001, 37, 336-338.	0.2	2
144	Barrier formation in a heterostructure formed of native oxide and p-InSe. Electrical and photoelectrical properties. Semiconductors, 2003, 37, 187-193.	0.2	2

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145	Surface barrier Sn-CuInSe2 junctions. Technical Physics Letters, 2004, 30, 402-403.	0.2	2
146	Asymmetric Current Transfer in Isotype n-In[sub 2]Se[sub 3]â€‰â^•n-InSe Heterocontacts. Technical Physics Letters, 2005, 31, 728.	0.2	2
147	Change of built-in-potential in heterostructures induced by X-ray irradiation. Nuclear Instruments & Methods in Physics Research B, 2006, 246, 118-121.	0.6	2
148	Mechanisms of current transfer and photosensitivity in Zn/CuInSe2 Schottky diodes. Technical Physics Letters, 2006, 32, 459-462.	0.2	2
149	Photosensitivity of heterojunctions formed by deposition of gum on a layered IIIâ€“VI semiconductor. Technical Physics, 2007, 52, 1178-1182.	0.2	2
150	Oxide films on the surface of GaSe doped with Cd or Dy. Inorganic Materials, 2008, 44, 680-686.	0.2	2
151	Electrical properties of magnesium-intercalated InSe. Inorganic Materials, 2009, 45, 846-850.	0.2	2
152	Hydrogen Sorption in Layered Nanoporous GaSe Crystals. NATO Science for Peace and Security Series C: Environmental Security, 2008, , 765-777.	0.1	2
153	Negative capacitance of native oxide films on (0001) InSe fracture surfaces. Inorganic Materials, 2011, 47, 847-852.	0.2	2
154	Asymmetric current flow in a native oxide/indium selenide heterostructure. Inorganic Materials, 2011, 47, 1178-1182.	0.2	2
155	Effect of annealing on the spectra of nuclear quadrupole resonance in gallium-indium selenides and characteristics of structures based on these materials. Semiconductors, 2012, 46, 1145-1151.	0.2	2
156	Sensitive elements of pressure transducers made of layered intercalated InSe, GaSe, and Bi2Te3 crystals. Technical Physics, 2013, 58, 1840-1843.	0.2	2
157	Electrical and optical properties of Al3+-intercalated InSe and GaSe. Inorganic Materials, 2013, 49, 22-27.	0.2	2
158	Morphology, chemical composition, and electrical characteristics of hybrid (Ni-C) nanocomposite structures grown on the van der Waals GaSe(0001) surface. Physics of the Solid State, 2014, 56, 2118-2130.	0.2	2
159	Formation of PbMnI2 alloys: Structural, photoluminescence and nuclear quadrupole resonance studies. Journal of Alloys and Compounds, 2020, 824, 153985.	2.8	2
160	Anomalous Anisotropic Magnetoresistance And Magnetization In Mn3.69Bi95.69Fe0.62. East European Journal of Physics, 2017, , .	0.1	2
161	Effect of Electron Irradiation on Conductivity Anisotropy in n-InSe. Journal of Nano- and Electronic Physics, 2017, 9, 06013-1-06013-5.	0.2	2
162	Hall-Coefficient Sign Inversion, Electrical Conductivity, and Its Anisotropy in Highly Intercalated NaxInSe Single Crystals. Physica Status Solidi A, 1989, 114, 293-298.	1.7	1

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163	The Te Intercalation Effect on the Electrical Properties of Indium Monoselenide. Physica Status Solidi (B): Basic Research, 1989, 154, K151.	0.7	1
164	The effect of intercalation on the exction spectrum and structure of layered single crystals. Russian Physics Journal, 1992, 35, 935-939.	0.2	1
165	Oxide-p-InSe heterojunctions on (110)-oriented InSe crystal substrates. Technical Physics Letters, 2001, 27, 424-426.	0.2	1
166	Properties of bismuth selenide intercalated with lithium from a solution of n-C4H9Li. Physics of the Solid State, 2001, 43, 1442-1444.	0.2	1
167	Temperature Dependence of Optical Energy Gap of Gallium Selenide. Journal of Wide Bandgap Materials, 2001, 8, 251-259.	0.1	1
168	Obtaining of Activated Carbon Materials for Supercapacitors. Molecular Crystals and Liquid Crystals, 2002, 388, 91-94.	0.4	1
169	Intercalation of Bismuth Chalcogenides with Molecular Fluorine. Inorganic Materials, 2002, 38, 25-27.	0.2	1
170	Anomalies in static and dynamic conductivity of indium monoselenide. Semiconductors, 2003, 37, 134-139.	0.2	1
171	Electrical properties of the p +-Bi2Te3-p-GaSe isotype heterostructure. Semiconductors, 2003, 37, 172-177.	0.2	1
172	On the mechanism of current passage in metal/p-CuInSe2 structures. Technical Physics, 2004, 49, 658-659.	0.2	1
173	Optical and electrical properties of turpentine films. Technical Physics, 2005, 50, 787-789.	0.2	1
174	Photovoltaic Effect in the Anisotype GaSe-InSe Heterojunctions Under Pressure. Materials Research Society Symposia Proceedings, 2005, 865, 511.	0.1	1
175	Current instability with Z- and N-shaped current-voltage characteristics in inhomogeneous In2Se3 crystals. Technical Physics Letters, 2009, 35, 569-572.	0.2	1
176	Electric performance and photosensitivity of heterostructures prepared by thermal decomposition of a gallium nitrate aqueous solution on an indium selenide (0001) cleaved surface. Technical Physics, 2009, 54, 397-401.	0.2	1
177	Anisotropy of resistivity in Bi93.99Mn6Fe0.01. Low Temperature Physics, 2015, 41, 314-316.	0.2	1
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